

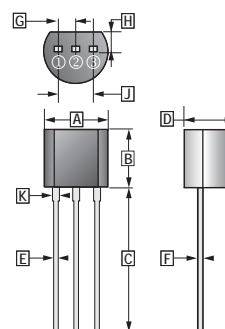
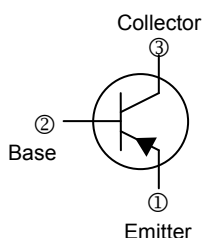
RoHS Compliant Product

A suffix of "-C" specifies halogen & lead-free

FEATURES

- High voltage transistors

TO-92



REF.	Millimeter	
	Min.	Max.
A	4.40	4.70
B	4.30	4.70
C	12.70	-
D	3.30	3.81
E	0.36	0.56
F	0.36	0.51
G	1.27 TYP.	
H	1.10	-
J	2.42	2.66
K	0.36	0.76

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector to Base Voltage	V _{CB0}	-350	V
Collector to Emitter Voltage	V _{CEO}	-350	V
Emitter to Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-0.5	A
Collector Power Dissipation	P _C	0.625	W
Thermal resistance, junction to ambient	R _{θJA}	200	°C / W
Junction, Storage Temperature	T _J , T _{STG}	150, -55~150	°C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITION
Collector to Base Breakdown Voltage	V _{(BR)CBO}	-350	-	-	V	I _C = -100μA, I _E = 0A
Collector to Emitter Breakdown Voltage	V _{(BR)CEO} *	-350	-	-	V	I _C = -1mA, I _B = 0A
Emitter to Base Breakdown Voltage	V _{(BR)EBO}	-5	-	-	V	I _E = -10μA, I _C = 0A
Collector Cut-Off Current	I _{CBO}	-	-	-50	nA	V _{CB} = -250V, I _E = 0 A
Emitter Cut-Off Current	I _{EBO}	-	-	-50	nA	V _{EB} = -4V, I _C = 0 mA
DC Current Gain	h _{FE} *	20	-	-	V	V _{CE} = -10V, I _C = -1mA
		30	-	-		V _{CE} = -10V, I _C = -10mA
		30	-	200		V _{CE} = -10V, I _C = -30mA
		20	-	200		V _{CE} = -10V, I _C = -50mA
		15	-	-		V _{CE} = -10V, I _C = -100mA
Collector to Emitter Saturation Voltage	V _{CE(sat)} *	-	-	-0.3	V	I _C = -10mA, I _B = -1mA
		-	-	-0.35		I _C = -20mA, I _B = -2mA
		-	-	-0.5		I _C = -30mA, I _B = -3mA
		-	-	-1.0		I _C = -50mA, I _B = -5mA
Base to Emitter Saturation Voltage	V _{BE(sat)} *	-	-	-0.75	V	I _C = -10mA, I _B = -1mA
		-	-	-0.85		I _C = -20mA, I _B = -2mA
		-	-	-0.9		I _C = -30mA, I _B = -3mA
Base to Emitter voltage	V _{BE(on)} *	-	-	-2	V	V _{CE} = -10V, I _C = -100mA
Collector-Base Capacitance	C _{cb}	-	-	6	pF	V _{CB} = -20V, I _E = 0A, f=1MHz
Emitter-Base Capacitance	C _{eb}	-	-	80	pF	V _{EB} = -0.5V, I _C = 0A, f=1MHz
Transition Frequency	f _T *	40	-	200	MHz	V _{CE} = -20V, I _C = -10mA, f=20MHz

*Pulse test : Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

CHARACTERISTIC CURVES

